

2A, 26V, 380kHz, Asynchronous Step-Down Converter

#### **Features**

- Wide Input Voltage from 4.5V to 26V
- Output Current up to 2A
- Adjustable Output Voltage from 0.8V to 90%V<sub>IN</sub>
  - 0.8V Reference Voltage
  - ±2.5% System Accuracy
- 100mWIntegrated P-Channel Power MOSFET
- High Efficiency up to 91%
  - Pulse-Skipping Mode (PSM) / PWM Mode Operation
- Current-Mode Operation
  - Stable with Ceramic Output Capacitors
  - Fast Transient Response
- Power-On-Reset Monitoring
- Fixed 380kHz Switching Frequency in PWM Mode
- Built-in Digital Soft-Start
- Output Current-Limit Protection with Frequency Foldback
- 70% Under-Voltage Protection
- Over-Temperature Protection
- <5mA Quiescent Current During Shutdown</li>
- SOP-8 Package
- Lead Free and Green Devices Available (RoHS Compliant)

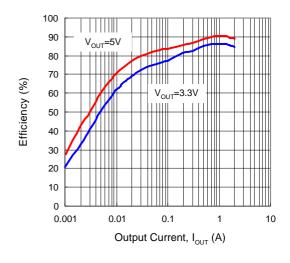
## **Applications**

- LCD Monitor / TV
- Set-Top Box
- Portable DVD
- Wireless LAN
- ADSL, Switch HUB
- Notebook Computer
- Step-Down Converters Requiring High Efficiency and 2A Output Current

## **General Description**

The APW7085 is a 2A, asynchronous, step-down converter with integrated  $100m\Omega$  P-channel MOSFET. The device, with current-mode control scheme, can convert 4.5~26V input voltage to the output voltage adjustable from 0.8 to 90%  $\rm V_{IN}$  to provide excellent output voltage regulation.

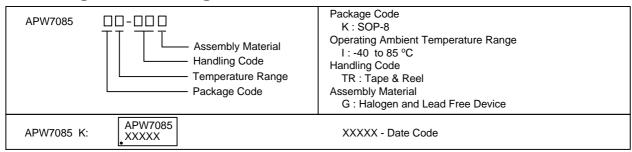
The APW7085 regulates the output voltage in automatic PSM/PWM mode operation, depending on the output current, for high efficiency operation over light to full load current. The APW7085 is also equipped with power-on-reset, soft-start, and whole protections (under-voltage, over- temperature, and current-limit) into a single package. In shutdown mode, the supply current drops below  $5\mu A$ . This device, available in a 8-pin SOP-8 package, provides a very compact system solution with minimal external components.



ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

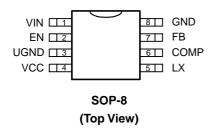


## Ordering and Marking Information

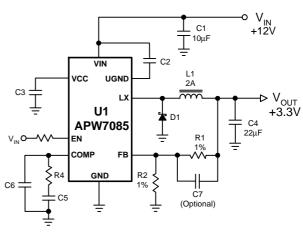


Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

## **Pin Configuration**



## **Simplified Application Circuit**



## Absolute Maximum Ratings (Note 1)

Symbol	Parameter	Rating	Unit	
V <sub>IN</sub>	VIN Supply Voltage (VIN to GND)		-0.3 ~ 30	V
V	LX to GND Voltage	> 100ns	-2 ~ V <sub>IN</sub> +0.3	V
$V_{LX}$	LX to GND voltage	< 100ns	-5 ~ V <sub>IN</sub> +6	V
M	VCC Supply Voltage (VCC to CND)	V <sub>IN</sub> > 6.2V	-0.3 ~ 6.5	V
V <sub>CC</sub>	VCC Supply Voltage (VCC to GND)	V <sub>IN</sub> ≤ 6.2V	< V <sub>IN</sub> +0.3	V
$V_{UGND\_GND}$	UGND to GND Voltage	-0.3 ~ V <sub>IN</sub> +0.3	V	
$V_{VIN\_UGND}$	VIN to UGND Voltage		-0.3 ~ 6.5V	V
	EN to GND Voltage		20	V
	FB, COMP to GND Voltage		-0.3 ~ V <sub>CC</sub> +0.3	V
	Maximum Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C	
$T_{SDR}$	Maximum Lead Soldering Temperature, 10 Second	260	°C	

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



### **Thermal Characteristics**

Symbol	Parameter	Typical Value	Unit
$\theta_{JA}$	Junction-to-Ambient Resistance in free air (Note 2) SOP-8	80	°C/W

Note 2:  $\theta_{JA}$  is measured with the component mounted on a high effective thermal conductivity test board in free air.

## **Recommended Operating Conditions** (Note 3)

Symbol	Parameter	Range	Unit
V <sub>IN</sub>	VIN Supply Voltage	4.5 ~ 26	V
	VCC Supply Voltage	4.0 ~ 5.5	V
V <sub>OUT</sub>	Converter Output Voltage	0.8 ~ 90% V <sub>IN</sub>	V
I <sub>OUT</sub>	Converter Output Current	0 ~ 2	Α
	VCC Input Capacitor	0.22 ~ 2.2	μF
	VIN-to-UGND Input Capacitor	0.22 ~ 2.2	μF
T <sub>A</sub>	Ambient Temperature	-40 ~ 85	°C
TJ	Junction Temperature	-40 ~ 125	°C

Note 3: Refer to the typical application circuits.

## **Electrical Characteristics**

Refer to the typical application circuits. These specifications apply over  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V and  $T_{A}$ = -40 ~ 85°C, unless otherwise specified.  $V_{CC}$  is regulated by an internal regulator. Typical values are at  $T_{A}$ =25°C.

Comple at	Danamatan	Test Conditions		APW7085			
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
SUPPLY	CURRENT	·	•				
I <sub>VIN</sub>	VIN Supply Current	V <sub>FB</sub> = 0.85V, V <sub>EN</sub> =3V, LX=Open	-	1.0	2.0	mA	
I <sub>VIN_SD</sub>	VIN Shutdown Supply Current	V <sub>EN</sub> = 0V, V <sub>IN</sub> =26V	-	-	5	μΑ	
I <sub>VCC</sub>	VCC Supply Current	$V_{EN} = 3V$ , $V_{CC} = 5.0V$ , $V_{FB} = 0.85V$	-	0.7	-	mA	
I <sub>VCC_SD</sub>	VCC Shutdown Supply Current	$V_{EN} = 0V, V_{CC} = 5.0V$	-	-	1	μΑ	
VCC 4.2V	LINEAR REGULATOR		-				
	Output Voltage	V <sub>IN</sub> = 5.2 ~ 26V, I <sub>O</sub> = 0 ~ 8mA	4.0	4.2	4.5	V	
	Load Regulation	I <sub>O</sub> = 0 ~ 8mA	-60	-40	0	mV	
	Current-Limit	V <sub>CC</sub> > POR Threshold	8	-	30	mA	
VIN-TO-U	GND 5.5V LINEAR REGULATOR		-				
	Output Voltage (V <sub>VIN-UGND</sub> )	$V_{IN} = 6.2 \sim 26 V$ , $I_O = 0 \sim 10 mA$	5.3	5.5	5.7	V	
	Load Regulation	I <sub>O</sub> = 0 ~ 10mA	-80	-60	0	mV	
	Current-Limit	V <sub>IN</sub> = 6.2 ~ 26V	10	-	30	mA	
POWER-0	ON-RESET (POR) AND LOCKOUT V	OLTAGE THRESHOLDS	-				
	VCC POR Voltage Threshold	V <sub>CC</sub> rising	3.7	3.9	4.1	V	
	VCC POR Hysteresis		-	0.15	-	V	
	EN Lockout Voltage Threshold	V <sub>EN</sub> rising	2.3	2.5	2.7	V	
	EN Lockout Hysteresis		-	0.2	-	V	



# **Electrical Characteristics (Cont.)**

Refer to the typical application circuits. These specifications apply over  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V and  $T_{A}$ = -40 ~ 85°C, unless otherwise specified.  $V_{CC}$  is regulated by an internal regulator. Typical values are at  $T_{A}$ =25°C.

Symbol	Parameter	Test Conditions		APW7085			
Symbol	Faranietei	rest conditions	Min.	Тур.	Max.	Unit	
POWER-	ON-RESET (POR) AND LOCKOUT V	DLTAGE THRESHOLDS (CONT.)		•	•		
	VIN-to-UGND Lockout Voltage Threshold	V <sub>VIN-UGND</sub> rising	-	3.5	-	٧	
	VIN-to-UGND Lockout Hysteresis		-	0.2	-	V	
REFERE	NCE VOLTAGE	•		,	•		
$V_{REF}$	Reference Voltage		-	0.8	-	V	
		$T_J = 25^{\circ}C, I_{OUT}=0A, V_{IN}=12V$	-1.0	-	+1.0		
	Output Voltage Accuracy	$T_J = -40 \sim 125^{\circ}C$ , $I_{OUT} = 0 \sim 2A$ , $V_{IN} = 4.5 \sim 26V$	-2.5	-	+2.5	%	
	Line Regulation	V <sub>IN</sub> = 4.5V to 26V, I <sub>OUT</sub> = 0A	-	0.36	-	%	
	Load Regulation	I <sub>OUT</sub> = 0 ~ 2A	=	0.4	-	%	
OSCILLA	TOR AND DUTY						
Fosc	Free Running Frequency	V <sub>IN</sub> = 4.5 ~ 26V	340	380	420	kHz	
	Foldback Frequency	$V_{FB} = 0V$	-	80	-	kHz	
	Maximum Converter's Duty Cycle		=	93	-	%	
	Minimum Pulse Width of LX	V <sub>IN</sub> = 4.5 ~ 26V	-	200	-	ns	
CURREN	T-MODE PWM CONVERTER	•					
Gm	Error Amplifier Transconductance		-	400	-	μA/V	
	Error Amplifier DC Gain	COMP = Open	60	80	-	dB	
	Current-Sense Resistance		-	0.2	-	Ω	
	P-Channel Power MOSFET Resistance	T <sub>J</sub> =25°C	-	100	140	mΩ	
PROTEC	TIONS	•					
I <sub>LIM</sub>	P-Channel Power MOSFET Current-limit	Peak Current	3	4	5	А	
$V_{\text{UV}}$	FB Under-Voltage Threshold	V <sub>FB</sub> falling	66	70	74	%	
	FB Under-Voltage Hysteresis		-	40	-	mV	
	FB Under-Voltage Debounce		-	2	-	μs	
T <sub>OTP</sub>	Over-Temperature Trip Point		=	150	-	°C	
	Over-Temperature Hysteresis		-	50	-	°C	
SOFT-ST	ART, ENABLE AND INPUT CURRENT	rs					
t <sub>SS</sub>	Soft-Start Interval		9	10.8	12	ms	
	Preceding Delay before Soft-Start		9	10.8	12	ms	
	EN Shutdown Voltage Threshold	V <sub>EN</sub> falling, V <sub>IN</sub> = 4 ~ 26V	-	-	0.8	V	
	EN Enable Voltage Threshold	V <sub>EN</sub> rising, V <sub>IN</sub> = 4 ~ 26V	2.1	-	-	V	
	EN Pin Clamped Voltage	I <sub>EN</sub> =10mA	12	-	17	V	
	P-Channel Power MOSFET Leakage Current	$V_{EN} = 0V, V_{LX} = 0V, V_{IN} = 26V$	-	-	4	μА	



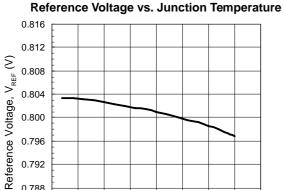
# **Electrical Characteristics (Cont.)**

Refer to the typical application circuits. These specifications apply over  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V and  $T_{A}$ = -40 ~ 85°C, unless otherwise specified.  $V_{CC}$  is regulated by an internal regulator. Typical values are at  $T_{A}$ =25°C.

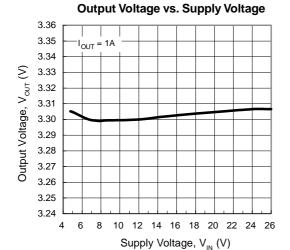
Symbol	Parameter	Test Conditions		Unit				
Syllibol	raidilietei	rest conditions	Min.	Тур.	Max.	Ollit		
SOFT-STA	SOFT-START, ENABLE AND INPUT CURRENTS (CONT.)							
I <sub>FB</sub>	FB Pin Input Current	$V_{FB} = 0.8V$	-100	-	+100	nA		
I <sub>EN</sub>	EN Pin Input Current	V <sub>EN</sub> < 3V	-500	-	+500	nA		

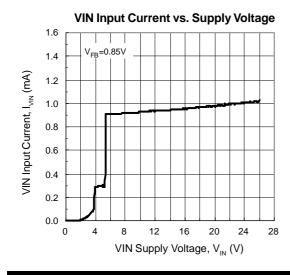


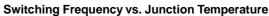
## **Typical Operating Characteristics**

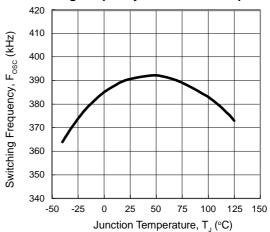


0.796 0.792 0.788 -25 25 50 75 100 125 -50 0 Junction Temperature, T, (°C)

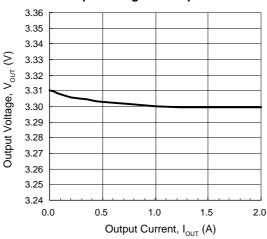




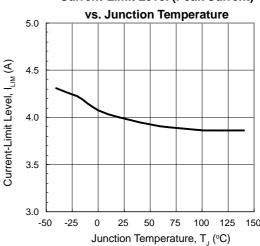




#### **Output Voltage vs. Output Current**

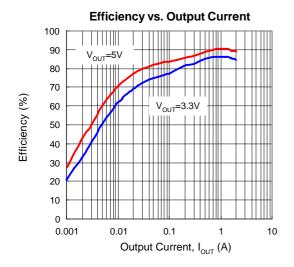


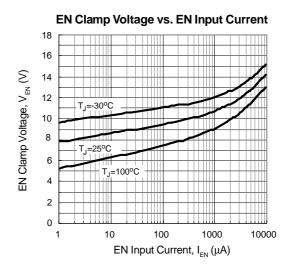
#### **Current-Limit Level (Peak Current)**





# **Typical Operating Characteristics (Cont.)**



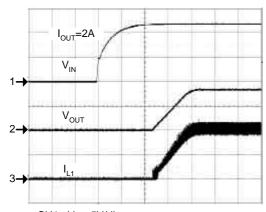




## **Operating Waveforms**

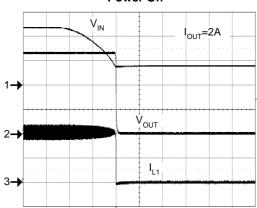
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=10 $\mu$ H)





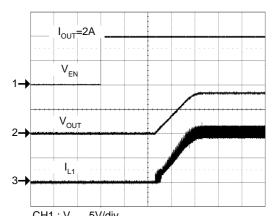
 $\begin{array}{l} \text{CH1: V}_{\text{IN}} \text{ , 5V/div} \\ \text{CH2: V}_{\text{OUT}} \text{ , 2V/div} \\ \text{CH3: I}_{\text{L1}} \text{ , 1A/div} \\ \text{Time: 5ms/div} \end{array}$ 

#### **Power Off**



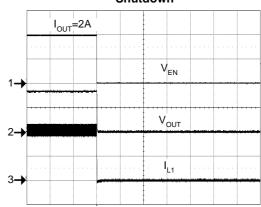
 $\begin{array}{l} \text{CH1: V}_{\text{IN}} \text{ , 5V/div} \\ \text{CH2: V}_{\text{OUT}} \text{ , 1V/div} \\ \text{CH3: I}_{\text{L1}} \text{ , 1A/div} \\ \text{Time: 5ms/div} \end{array}$ 

## ΕN



 $\begin{aligned} & \text{CH1:V}_{\text{EN}} \text{, 5V/div} \\ & \text{CH2:V}_{\text{OUT}} \text{, 2V/div} \\ & \text{CH3:I}_{\text{L1}} \text{, 1A/div} \\ & \text{Time:5ms/div} \end{aligned}$ 

## Shutdown



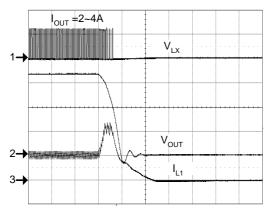
 $\begin{array}{l} CH1: V_{EN} \text{ , } 5V/div \\ CH2: V_{OUT} \text{ , } 2V/div \\ CH3: I_{L1} \text{ , } 1A/div \\ Time: 5ms/div \end{array}$ 



## **Operating Waveforms (Cont.)**

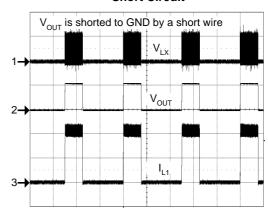
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=10 $\mu$ H)

#### **Over Current**



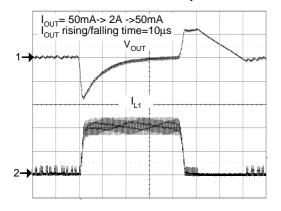
 $\begin{aligned} &CH1: V_{LX} \,,\, 10V/div\\ &CH2: V_{OUT} \,,\, 1V/div\\ &CH3: I_{L1} \,,\, 2A/div\\ &Time: 50\mu s/div \end{aligned}$ 

#### **Short Circuit**



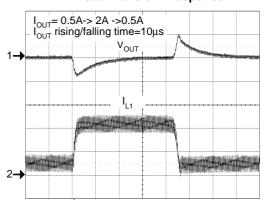
 $\begin{aligned} &\text{CH1: V}_{\text{LX}} \text{ , 10V/div} \\ &\text{CH2: V}_{\text{OUT}} \text{ , 50mV/div} \\ &\text{CH3: I}_{\text{L1}} \text{ , 2A/div} \\ &\text{Time: 50ms/div} \end{aligned}$ 

#### **Load Transient Response**



CH1 :  $V_{OUT}$  , 200mV/div CH2 :  $I_{L1}$  , 1A/div Time : 50 $\mu$ s/div

#### **Load Transient Response**



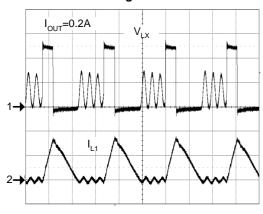
CH1 :  $V_{OUT}$  , 200mV/div CH2 :  $I_{L1}$  , 1A/div Time : 50 $\mu$ s/div



## **Operating Waveforms (Cont.)**

(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=10 $\mu$ H )

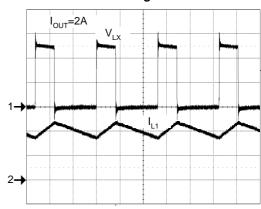
#### **Switching Waveform**



 $\mbox{CH1}:\mbox{V}_{\mbox{\scriptsize LX}}$  , 5V/div  $\mathrm{CH2}: \mathrm{I}_{\mathrm{L1}}$  , 200mA/div

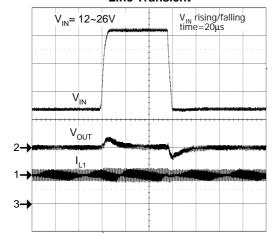
Time: 1µs/div

#### **Switching Waveform**



 $\mathrm{CH1}: \mathrm{V}_{\mathrm{LX}}$  , 5V/div CH2 : I<sub>L1</sub> , 1A/div Time : 1µs/div

#### **Line Transient**



 $\mbox{CH1}:\mbox{V}_{\mbox{\footnotesize{IN}}}$  , 5V/div

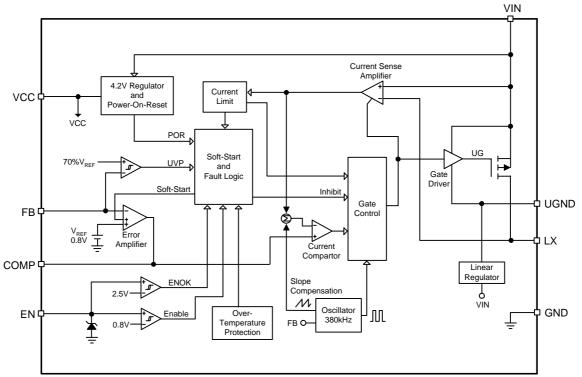
CH2 :  $V_{OUT}$  , 100mA/div (Voffset=3.3V) CH3 :  $I_{L1}$  , 2A/div Time : 100 $\mu$ s/div



# **Pin Description**

PIN	NAME	FUNCTION
1	VIN	Power Input. VIN supplies the power (4.5V to 26V) to the control circuitry, gate driver and step-down converter switch. Connecting a ceramic bypass capacitor and a suitably large capacitor between VIN and GND eliminates switching noise and voltage ripple on the input to the IC.
2	EN	Enable Input. EN is a digital input that turns the regulator on or off. Drive EN high to turn on the regulator, drive it low to turn it off. Pull up with $100 \mathrm{k}\Omega$ resistor for automatic startup.
3	UGND	Gate driver power ground of the P-channel Power MOSFET. A linear regulator regulates a 5.5V voltage between VIN and UGND to supply power to P-channel MOSFET gate driver. Connect a ceramic capacitor (1µF typ.) between VIN and UGND for noise decoupling and stability of the linear regulator.
4	VCC	Bias input and 4.2V linear regulator's output. This pin supplies the bias to some control circuits. The 4.2V linear regulator converts the voltage on VIN to 4.2V to supply the bias when no external 5V power supply is connected with VCC. Connect a ceramic capacitor (1µF typ.) between VCC and GND for noise decoupling and stability of the linear regulator.
5	LX	Power Switching Output. LX is the Drain of the P-channel MOSFET to supply power to the output. Connect the pin to output LC filter.
6	СОМР	Output of error amplifier. Connect a series RC network from COMP to GND to compensate the regulation control loop. In some cases, an additional capacitor from COMP to GND is required for noise decoupling.
7	FB	Feedback Input. The IC senses feedback voltage via FB and regulate the voltage at 0.8V. Connecting FB with a resistor-divider from the output set the output voltage in the range from 0.8V to 90% V <sub>IN</sub> .
8	GND	Power and Signal Ground.

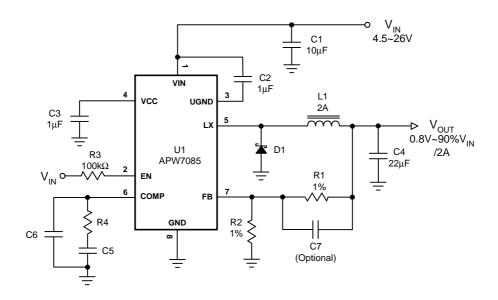
# **Block Diagram**





# **Typical Application Circuits**

### 1. 4.5~26V Single Power Input Step-down Converter (with Ceramic Input/Output Capacitors)



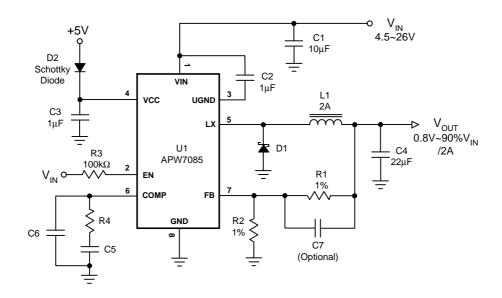
Recommended Feedback Compensation Network Components List:

VIN (V)	VOUT (V)	L1 ( <b>nH</b> )	C4 ( <b>nF</b> )	C4 ESR (m <b>W</b> )	R1 (k <b>W</b> )	R2 (k <b>W</b> )	C7 (pF)	R4 (k <b>W</b> )	C5 (pF)	C6 (pF)
24	12	15	22	5	140	10	15	100	820	22
24	12	15	44	3	140	10	15	200	820	22
24	5	10	22	5	63.4	12	22	43	1800	22
24	5	10	44	3	63.4	12	22	82	1800	22
12	5	10	22	5	63.4	12	30	43	1000	22
12	5	10	44	3	63.4	12	30	82	1000	22
12	3.3	10	22	5	47	15	39	27	1500	22
12	3.3	10	44	3	47	15	39	56	1500	22
12	2	4.7	22	5	30	20	39	18	2200	22
12	2	4.7	44	3	30	20	39	36	2200	22
12	1.2	3.3	22	5	7.5	15	100	10	3600	22
12	1.2	3.3	44	3	7.5	15	100	20	3600	22
5	3.3	3.3	22	5	47	15	47	27	560	22
5	3.3	3.3	44	3	47	15	47	56	560	22
5	1.2	2.2	22	5	7.5	15	200	10	1500	22
5	1.2	2.2	44	3	7.5	15	200	20	1500	22
5	0.8	2.2	22	5	0	NC	NC	6.8	2200	22
5	0.8	2.2	44	3	0	NC	NC	15	2200	22

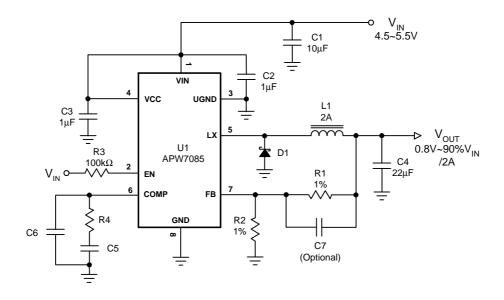


# **Typical Application Circuits (Cont.)**

## 2. Dual Power Inputs Step-down Converter (V<sub>IN</sub>=4.5~26V)



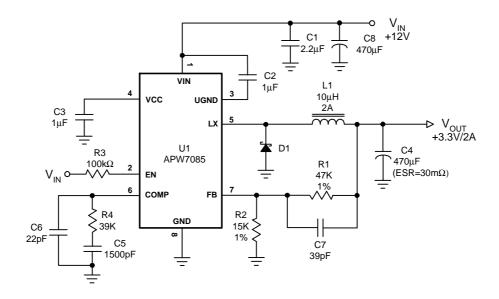
### 3. 4.5~5.5V Single Power Input Step-down Converter



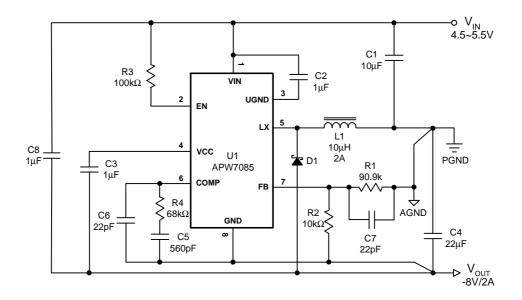


# **Typical Application Circuits (Cont.)**

4. +12V Single Power Input Step-down Converter (with Electrolytic Input/Output Capacitors)



## 5. -8V Inverting Converter with 4.5~5.5V Single Power Input





## **Function Description**

#### **Main Control Loop**

The APW7085 is a constant frequency current mode switching regulator. During normal operation, the internal P-channel power MOSFET is turned on each cycle when the oscillator sets an internal RS latch and would be turned off when an internal current comparator (ICMP) resets the latch. The peak inductor current at which ICMP resets the RS latch is controlled by the voltage on the COMP pin, which is the output of the error amplifier (EAMP). An external resistive divider connected between  $V_{\text{OUT}}$  and ground allows the EAMP to receive an output feedback voltage  $V_{\text{FB}}$  at FB pin. When the load current increases, it causes a slight decrease in  $V_{\text{FB}}$  relative to the 0.8V reference, which in turn causes the COMP voltage to increase until the average inductor current matches the new load current.

# VCC Power-On-Reset (POR) and EN Undervoltage Lockout

The APW7085 keeps monitoring the voltage on VCC pin to prevent wrong logic operations which may occur when VCC voltage is not high enough for the internal control circuitry to operate. The VCC POR has a rising threshold of 3.9V (typical) with 0.15V of hysteresis.

An external undervoltage lockout (UVLO) is sensed and programmed at the EN pin. The EN UVLO has a rising threshold of 2.5V with 0.2V of hysteresis. The EN UVLO should be programmed by connecting a resistive divider from VIN to EN to GND.

After the VCC, EN and VIN-to-UGND voltages exceed their respective voltage thresholds, the IC starts a start-up process and then ramps up the output voltage to the setting of output voltage. Connect a RC network from EN to GND to set a turn-on delay that can be used to sequence the output voltages of multiple devices.

#### VCC 4.2V Linear Regulator

VCC is the output terminal of the internal 4.2V linear regulator which is powered from VIN and provides power to the APW7085. The linear regulator designed to be stable with a low-ESR ceramic output capacitor powers the internal control circuitry. Bypass VCC to GND with a ceramic capacitor of at least  $0.22\mu F$ . Place the capacitor physically

close to the IC to provide good noise decoupling. The linear regulator is not intended for powering up any external loads. Do not connect any external loads to VCC. The linear regulator is also equipped with current-limit protection to protect itself during over-load or short-circuit conditions on VCC pin.

#### VIN-to-UGND 5.5V Linear Regulator

The built-in 5.5V linear regulator regulates a 5.5V voltage between VIN and UGND pins to supply bias and gate charge for the P-channel Power MOSFET gate driver. The linear regulator is designed to be stable with a low-ESR ceramic output capacitor of at least 0.22 $\mu$ F. It is also equipped with current-limit function to protect itself during over-load or short-circuit conditions between VIN and UGND.

The APW7085 shuts off the output of the converters when the output voltage of the linear regulator is below 3.5V (typical). The IC resumes working by initiating a new soft-start process when the linear regulator's output voltage is above the undervoltage lockout voltage threshold.

#### **Digital Soft-Start**

The APW7085 has a built-in digital soft-start to control the output voltage rise and limit the input current surge during start-up. During soft-start, an internal ramp, connected to the one of the positive inputs of the error amplifier, rises up from 0V to 1V to replace the reference voltage (0.8V) until the ramp voltage reaches the reference voltage. The device is designed with a preceding delay about 10.8ms (typical) before soft-start process.

#### **Output Under-Voltage Protection**

In the process of operation, if a short-circuit occurs, the output voltage will drop quickly. Before the current-limit circuit responds, the output voltage will fall out of the required regulation range. The undervoltage continually monitors the FB voltage after soft-start is completed. If a load step is strong enough to pull the output voltage lower than the under-voltage threshold, the IC shuts down converter's output.

The under-voltage threshold is 70% of the nominal output voltage. The undervoltage comparator has a built-in



## **Function Description (Cont.)**

#### **Output Under-Voltage Protection (Cont.)**

2μs noise filter to prevent the chips from wrong UVP shutdown caused by noise. The under-voltage protection works in a hiccup mode without latched shutdown. The IC will initiate a new soft-start process at the end of the preceeding delay.

#### **Over-Temperature Protection (OTP)**

The over-temperature circuit limits the junction temperature of the APW7085. When the junction temperature exceeds  $T_J$ =+150°C, a thermal sensor turns off the power MOSFET, allowing the devices to cool. The thermal sensor allows the converter to start a start-up process and regulate the output voltage again after the junction temperature cools by 50°C. The OTP is designed with a 50°C hysteresis to lower the average  $T_J$  during continuous thermal overload conditions, increasing lifetime of the IC.

#### Enable/Shutdown

Driving EN to ground places the APW7085 in shutdown. When in shutdown, the internal power MOSFET turns off, all internal circuitry shuts down and the quiescent supply current of VIN reduces to  $<1\mu$ A (typical).

#### **Current-Limit Protection**

The APW7085 monitors the output current, flowing through the P-channel power MOSFET, and limits the current peak at current-limit level to prevent loads and the IC from damages during overload or short-circuit conditions.

#### Frequency Foldback

When the output is shortened to the ground, the frequency of the oscillator will be reduced to about 80kHz. This lower frequency allows the inductor current to safely discharge, thereby preventing current runaway. The oscillator's frequency will gradually increase to its designed rate when the feedback voltage on FB again approaches 0.8V.



## Application Information

#### **Power Sequencing**

The APW7085 can operate with sigle or dual power input (s).

In dual-power applications, the voltage ( $V_{\rm CC}$ ) applied at VCC pin must be lower than the voltage ( $V_{\rm IN}$ ) on VIN pin. The reason is the internal parasitic diode from VCC to VIN will conduct due to the forward-voltage between VCC and VIN. Therefore,  $V_{\rm IN}$  must be provided before  $V_{\rm CC}$ .

#### **Setting Output Voltage**

The regulated output voltage is determined by:

Vout = 
$$0.8 \cdot (1 + \frac{R1}{R2})$$
 (V)

Suggested R2 is in the range from 1K to  $20k\Omega$ . For portable applications, a  $10k\Omega$  resistor is suggested for R2. To prevent stray pickup, locate resistors R1 and R2 close to APW7085.

#### **Input Capacitor Selection**

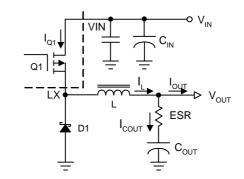
Each time, when the P-channel power MOSFET (Q1) turns on, small ceramic capacitors for high frequency decoupling and bulk capacitors is required to supply the surge current. The small ceramic capacitors have to be placed physically close to the VIN and between the VIN and the anode of the Schottky diode (D1).

The important parameters for the bulk input capacitor are the voltage rating and the RMS current rating. For reliable operation, select the bulk capacitor with voltage and current ratings above the maximum input voltage and largest RMS current required by the circuit. The capacitor voltage rating should be at least 1.25 times greater than the maximum input voltage and a voltage rating of 1.5 times is a conservative guideline. The RMS current ( $I_{RMS}$ ) of the bulk input capacitor is calculated as the following equation:

IRMS = IOUT 
$$\cdot \sqrt{D \cdot (1-D)}$$
 (A)

where D is the duty cycle of the power MOSFET.

For a through hole design, several electrolytic capacitors may be needed. For surface mount designs, solid tantalum capacitors can be used, but caution must be exercised with regard to the capacitor surge current rating.



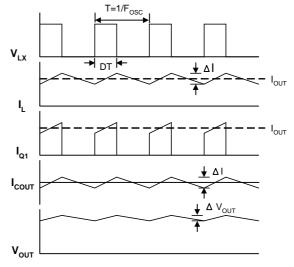


Figure 1. Converter Waveforms

#### **Output Capacitor Selection**

An output capacitor is required to filter the output and supply the load transient current. The filtering requirements are the functions of the switching frequency and the ripple current ( $\Delta I$ ). The output ripple is the sum of the voltages, having phase shift, across the ESR and the ideal output capacitor. The peak-to-peak voltage of the ESR is calculated as the following equations:

$$D = \frac{V_{OUT} + V_D}{V_{IN} + V_D} \qquad .....(1)$$

$$\Delta I = \frac{\text{Vout} \cdot (1 - D)}{\text{Fosc} \cdot L} \qquad ..........(2)$$

$$V_{ESR} = \Delta I \cdot ESR$$
 (V) ......(3)

where  $V_{\scriptscriptstyle D}$  is the forward voltage drop of the diode. The peak-to-peak voltage of the ideal output capacitor is

calculated as the following equations:



## **Application Information (Cont.)**

#### **Output Capacitor Selection (Cont.)**

$$\Delta V_{COUT} = \frac{\Delta I}{8 \cdot Fosc \cdot C_{OUT}} (V) \qquad .....(4)$$

For the applications, using bulk capacitors, the  $\Delta V_{\text{COUT}}$  is much smaller than the  $V_{\text{ESR}}$  and can be ignored. Therefore, the AC peak-to-peak output voltage ( $\Delta V_{\text{OUT}}$ ) is shown as below:

$$\Delta V_{OUT} = \Delta I \cdot ESR$$
 (V) ......(5)

For the applications, using ceramic capacitors, the V<sub>ESR</sub> is much smaller than the  $\Delta V_{COUT}$  and can be ignored. Therefore, the AC peak-to-peak output voltage ( $\Delta V_{OUT}$ ) is close to  $\Delta V_{COUT}$ .

The load transient requirements are the functions of the slew rate (di/dt) and the magnitude of the transient load current. These requirements are generally met with a mix of capacitors and careful layout. High frequency capacitors initially supply the transient and slow the current load rate seen by the bulk capacitors. The bulk filter capacitor values are generally determined by the ESR (Effective Series Resistance) and voltage rating requirements rather than actual capacitance requirements.

High frequency decoupling capacitors should be placed physically as close to the power pins of the load as possible. Be careful not to add inductance in the circuit board wiring that could cancel the usefulness of these low inductance components. An aluminum electrolytic capacitor's ESR value is related to the case size with lower ESR available in larger case sizes. However, the Equivalent Series Inductance (ESL) of these capacitors increases with case size and can reduce the usefulness of the capacitor to high slew-rate transient loading.

#### Inductor Value Calculation

The operating frequency and inductor selection are interrelated in that higher operating frequencies permit the use of a smaller inductor for the same amount of inductor ripple current. However, this is at the expense of efficiency due to an increase in MOSFET gate charge losses. The equation (2) shows that the inductance value has a direct effect on ripple current.

Accepting larger values of ripple current allows the use of low inductances but results in higher output voltage ripple and greater core losses. A reasonable starting point for setting ripple current is  $\Delta I \leq 0.4 \cdot I_{\text{OUT(MAX)}}$ . Remember, the maximum ripple current occurs at the maximum input voltage. The minimum inductance of the inductor is calculated by using the following equation:

$$\frac{V_{\text{OUT}} \cdot (V_{\text{IN}} - V_{\text{OUT}})}{380000 \cdot L \cdot V_{\text{IN}}} \le 1.2$$

$$L \ge \frac{V_{\text{OUT}} \cdot (V_{\text{IN}} - V_{\text{OUT}})}{456000 \cdot V_{\text{IN}}} \qquad (H) \qquad \qquad (6)$$
where  $V_{\text{IN}} = V_{\text{IN/MAX}}$ 

#### **Output Diode Selection**

The Schottky diode carries load current during the off-time. Therefore, the average diode current is dependent on the P-channel power MOSFET duty cycle. At high input voltages, the diode conducts most of the time. As  $V_{\rm IN}$  approaches  $V_{\rm OUT}$ , the diode conducts only a small fraction of the time. The most stressful condition for the diode is when the output is short-circuited. Therefore, it is important to adequately specify the diode peak current and average power dissipation so as not to exceed the diode ratings.

Under normal load conditions, the average current conducted by the diode is:

$$I_D = \frac{V_{IN} - V_{OUT}}{V_{IN} + V_D} \cdot I_{OUT}$$

The APW7085 is equipped with whole protections to reduce the power dissipation during short-circuit condition. Therefore, the maximum power dissipation of the diode is calculated from the maximum output current as:

$$P_{DIODE(MAX)} = V_D \cdot I_{D(MAX)}$$
  
where  $V_{OUT} = V_{OUT(MAX)}$ 

Remember to keep lead length short and observe proper grounding to avoid ringing and increased dissipation.



## **Layout Consideration**

In high power switching regulator, a correct layout is important to ensure proper operation of the regulator. In general, interconnecting impedance should be minimized by using short and wide printed circuit traces. Signal and power grounds are to be kept separating and finally combined using ground plane construction or single point grounding. Figure 2 illustrates the layout, with bold lines indicating high current paths. Components along the bold lines should be placed close together. Below is a checklist for your layout:

- Begin the layout by placing the power components first.
   Orient the power circuitry to achieve a clean power flow path. If possible, make all the connections on one side of the PCB with wide and copper filled areas.
- In Figure 2, the loops with same color bold lines conduct high slew rate current. These interconnecting impedances should be minimized by using wide and short printed circuit traces.
- 3. Keep the sensitive small signal nodes (FB, COMP) away from switching nodes (LX or others) on the PCB. Therefore, place the feedback divider and the feedback compensation network close to the IC to avoid switching noise. Connect the ground of feedback divider directly to the GND pin of the IC using a dedicated ground trace.
- 4. The VCC decoupling capacitor should be right next to the VCC and GND pins. Capacitor C2 should be connected as close to the VIN and UGND pins as possible.

5. Place the decoupling ceramic capacitor C1 near the VIN as close as possible. The bulk capacitors C8 are also placed near VIN. Use a wide power ground plane to connect the C1, C8, C4, and Schottky diode to provide a low impedance path between the components for large and high slew rate current.

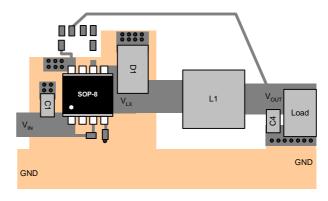


Figure 3. Recommended Layout Diagram

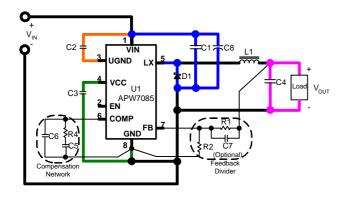
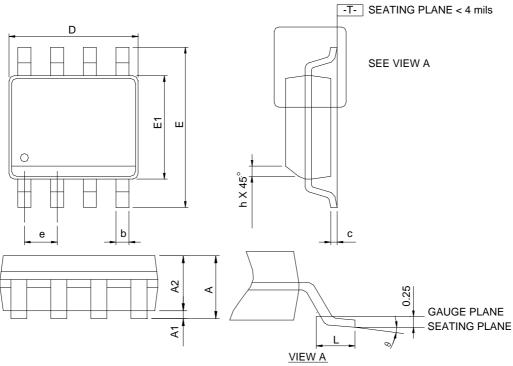


Figure 2. Current Path Diagram



# **Package Information**

### SOP-8



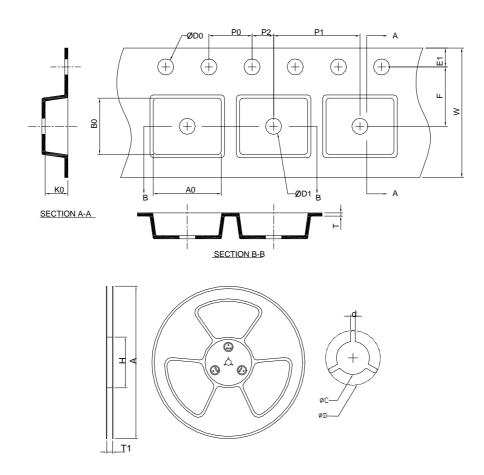
S	SOP-8						
SYMBOL	MILLIM	MILLIMETERS		HES			
Ō	MIN.	MAX.	MIN.	MAX.			
Α		1.75		0.069			
A1	0.10	0.25	0.004	0.010			
A2	1.25		0.049				
b	0.31	0.51	0.012	0.020			
С	0.17	0.25	0.007	0.010			
D	4.80	5.00	0.189	0.197			
Е	5.80	6.20	0.228	0.244			
E1	3.80	4.00	0.150	0.157			
е	1.27	BSC	0.050 BSC				
h	0.25	0.50	0.010	0.020			
L	0.40	1.27	0.016	0.050			
θ	0°	8°	0°	8°			

Note: 1. Follow JEDEC MS-012 AA.

- 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
- 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.



# **Carrier Tape & Reel Dimensions**



Application	Α	Н	<b>T</b> 1	С	d	D	W	E1	F
	330.0 €.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 <b>±</b> 0.30	1.75 ±0.10	5.5 ±0.05
SOP-8	P0	P1	P2	D0	D1	Т	A0	В0	K0
	4.0 <b>±</b> 0.10	8.0 <b>±</b> 0.10	2.0 <b>±</b> 0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 <b>±</b> 0.20	5.20 <b>±</b> 0.20	2.10 <b>£</b> 0.20

(mm)

## **Devices Per Unit**

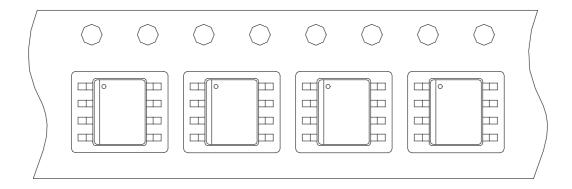
Package Type	Unit	Quantity	
SOP-8	Tape & Reel	2500	



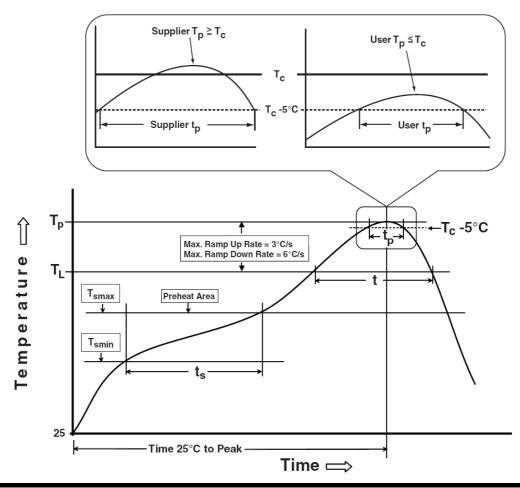
# **Taping Direction Information**

SOP-8





## **Classification Profile**





## **Classification Reflow Profiles**

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly				
Preheat & Soak Temperature min (T <sub>smin</sub> ) Temperature max (T <sub>smax</sub> ) Time (T <sub>smin</sub> to T <sub>smax</sub> ) (t <sub>s</sub> )	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds				
Average ramp-up rate (T <sub>smax</sub> to T <sub>P</sub> )	3 °C/second max.	3°C/second max.				
Liquidous temperature (T <sub>L</sub> ) Time at liquidous (t <sub>L</sub> )	183 °C 60-150 seconds	217 °C 60-150 seconds				
Peak package body Temperature (T <sub>p</sub> )*	See Classification Temp in table 1	See Classification Temp in table 2				
Time (t <sub>P</sub> )** within 5°C of the specified classification temperature (T <sub>c</sub> )	20** seconds	30** seconds				
Average ramp-down rate (T <sub>p</sub> to T <sub>smax</sub> )	6 °C/second max.	6 °C/second max.				
Time 25°C to peak temperature	6 minutes max.	8 minutes max.				
* Tolerance for peak profile Temperature (T ) is defined as a supplier minimum and a user maximum						

<sup>\*</sup> Tolerance for peak profile Temperature (Tp) is defined as a supplier minimum and a user maximum.

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm³ ³350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000	
<1.6 mm	260 °C	260 °C	260 °C	
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C	
≥2.5 mm	250 °C	245 °C	245 °C	

# **Reliability Test Program**

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ T <sub>j</sub> =125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C
НВМ	MIL-STD-883-3015.7	VHBM 2KV
MM	JESD-22, A115	VMM 200V
Latch-Up	JESD 78	10ms, 1 <sub>tr</sub> 100mA

<sup>\*\*</sup> Tolerance for time at peak profile temperature (tp) is defined as a supplier minimum and a user maximum.



### **Customer Service**

## **Anpec Electronics Corp.**

Head Office:

No.6, Dusing 1st Road, SBIP,

Hsin-Chu, Taiwan Tel: 886-3-5642000 Fax: 886-3-5642050

### Taipei Branch:

2F, No. 11, Lane 218, Sec 2 Jhongsing Rd., Sindian City, Taipei County 23146, Taiwan

Tel: 886-2-2910-3838 Fax: 886-2-2917-3838